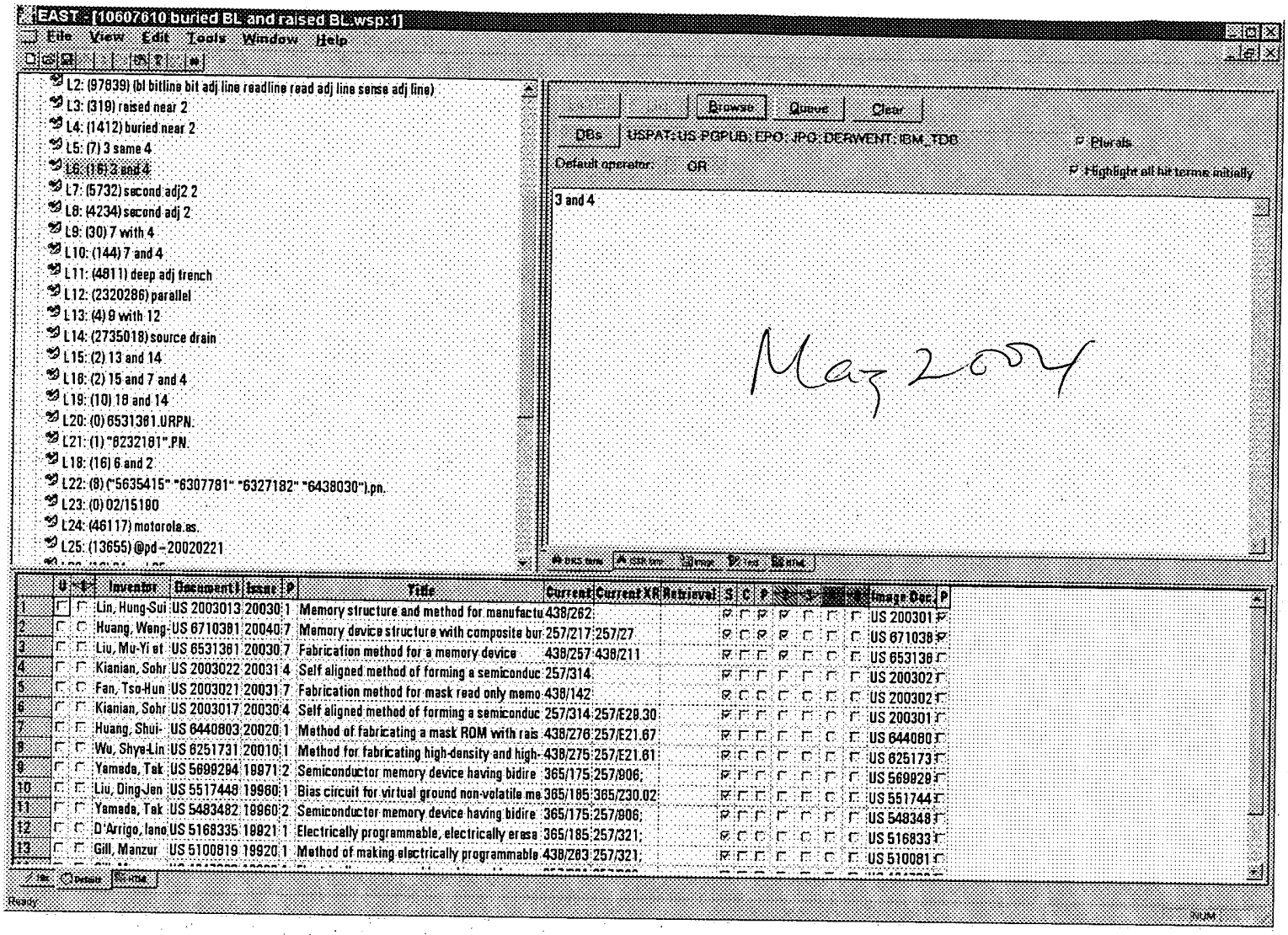
EAST - [10607610 buried BL and raised BL.wsp:1]
File View Edit Tools Window Help
L2: (97839) (bl bitline bit adj line readline read adj line sense adj line)
L3: (319) raised near 2
L4: (1412) buried near 2
L5: (7) 3 same 4
L6: (16) 3 and 4
L7: (5732) second adj2 2
L8: (4234) second adj 2
L9: (30) 7 with 4
L10: (144) 7 and 4
L11: (4811) deep adj trench
L12: (2320286) parallel
L13: (4) 9 with 12
L14: (2735018) source drain
L15: (2) 13 and 14
L16: (2) 15 and 7 and 4
L19: (10) 18 and 14
L20: (0) 6531361.URPN.
L21: (1) "6232181".PN.
L18: (16) 6 and 2
L22: (8) ("5635415" "6307781" "6327182" "6438030").pn.
L23: (0) 02/15180
L24: (46117) motorola.as.
L25: (13655) @pd>20020221
Browse
Queue
Clear
DBs
USPAT;US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
Plurals
Default operator: OR
Highlight all hit terms initially
3 and 4
May 2004
U
Inventor
Document I
Issue
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Title
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Current XR
Retrieval
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C
P
Image Doc.
1 Lin, Hung-Sui US 2003013 20030 1 Memory structure and method for manufactu 438/262; US 200301
2 Huang, Weng- US 6710381 20040 7 Memory device structure with composite bur 257/217;257/27 US 671038
3 Liu, Mu-Yi et US 6531361 20030 7 Fabrication method for a memory device 438/257;438/211 US 653136
4 Kianian, Sohr US 2003022 20031 4 Self aligned method of forming a semiconduc 257/314; US 200302
5 Fan, Tso-Hun US 2003021 20031 7 Fabrication method for mask read only memo 438/142; US 200302
6 Kianian, Sohr US 2003017 20030 4 Self aligned method of forming a semiconduc 257/314;257/E29.30 US 200301
7 Huang, Shui- US 6440803 20020 1 Method of fabricating a mask ROM with rais 438/276;257/E21.67 US 644080
8 Wu, Shye-Lin US 6251731 20010 1 Method for fabricating high-density and high- 438/275;257/E21.61 US 625173
9 Yamada, Tak US 5699294 19971 2 Semiconductor memory device having bidire 365/175;257/906; US 569929
10 Liu, Ding-Jen US 5517448 19960 1 Bias circuit for virtual ground non-volatile me 365/185;365/230.02 US 551744
11 Yamada, Tak US 5483482 19960 2 Semiconductor memory device having bidire 365/175;257/906; US 548348
12 D'Arrigo, Iano US 5168335 19821 1 Electrically programmable, electrically erasa 365/185;257/321; US 516833
13 Gill, Manzur US 5100819 19920 1 Method of making electrically programmable 438/263;257/321; US 510081
Ready
NUM